# **SQ2348ES**

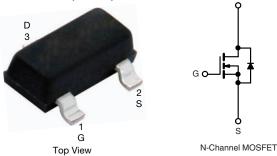


Vishay Siliconix

# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	30			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.024			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.032			
I <sub>D</sub> (A)	8			
Configuration	Single			

#### SOT-23 (TO-236)



#### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified <sup>c</sup>
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



COMPLIANT HALOGEN

#### Marking Code: 8Vxxx

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2348ES-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub>	= 25 °C, unles	s otherwise noted)	)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v
Continuous Drain Current	T <sub>C</sub> = 25 °C	I.	8	
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	5.3	
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	3.8	A	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	32		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	15.5	
Single Pulse Avalanche Energy		E <sub>AS</sub>	12	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	3	W
Maximum Fower Dissipation ~	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1	vv
Operating Junction and Storage Temperature Rang	je	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	166	°C/W
Junction-to-Foot (Drain)		R <sub>thJF</sub>	50	0/10

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. When mounted on 1" square PCB (FR4 material).

c. Parametric verification ongoing.

1

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**SQ2348ES** 

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		•		1	<b>I</b>	1	1
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> :	= 0 V, I <sub>D</sub> = 250 μΑ	30	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	1.5	2.0	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	: 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	10	-	-	Α
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 10 V$	I <sub>D</sub> = 12 A	-	0.020	0.024	Ω
	P	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A, T <sub>J</sub> = 125 °C	-	-	0.036	
	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 12 A, T <sub>J</sub> = 175 °C	-	-	0.042	
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 8 A	-	0.026	0.032	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 3 A		-	10	-	S
Dynamic <sup>b</sup>	•	•		•	•	•	
Input Capacitance	C <sub>iss</sub>			-	430	540	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 15 V, f = 1 MHz	-	100	125	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	40	50	
Total Gate Charge <sup>c</sup>	Qg			-	7.95	14.5	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{GS} = 10 \text{ V}$ $V_{DS} = 15 \text{ V}, I_D = 5.5 \text{ A}$		1.6	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	1.3	-	1
Gate Resistance	Rg	f = 1 MHz		8.65	17.3	27	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	4.5	7	
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:V_DD} \begin{array}{l} V_{DD} = 15 \ V, \ R_L = 3.4 \ \Omega \\ I_D \cong 4.4 \ A, \ V_GEN = 10 \ V, \ R_g = 1 \ \Omega \end{array}$		-	8	12	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	21	32	
Fall Time <sup>c</sup>	t <sub>f</sub>	7		-	6	9	1
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	32	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	3.5 A, V <sub>GS</sub> = 0 V	-	0.8	1.2	V
					•		

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

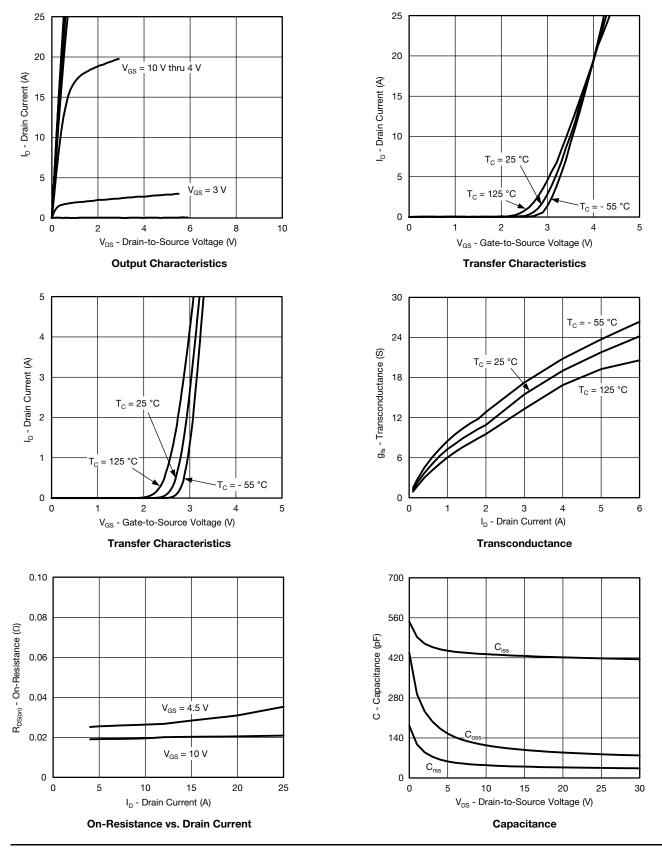
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



**SQ2348ES** 

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## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



S15-1218-Rev. B, 21-May-15

3

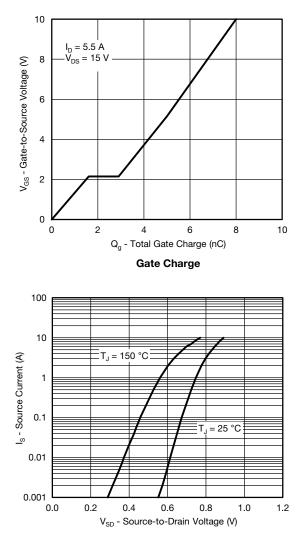
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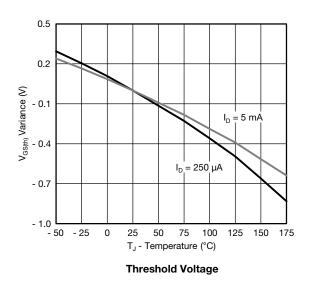


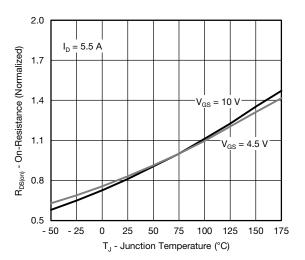
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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

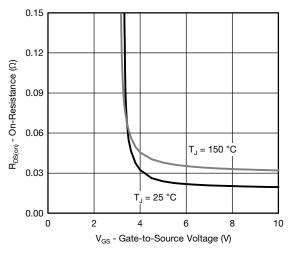


Source Drain Diode Forward Voltage

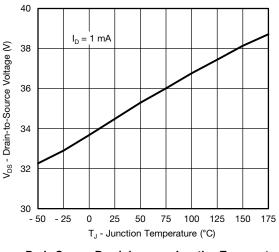




**On-Resistance vs. Junction Temperature** 







Drain Source Breakdown vs. Junction Temperature

S15-1218-Rev. B, 21-May-15

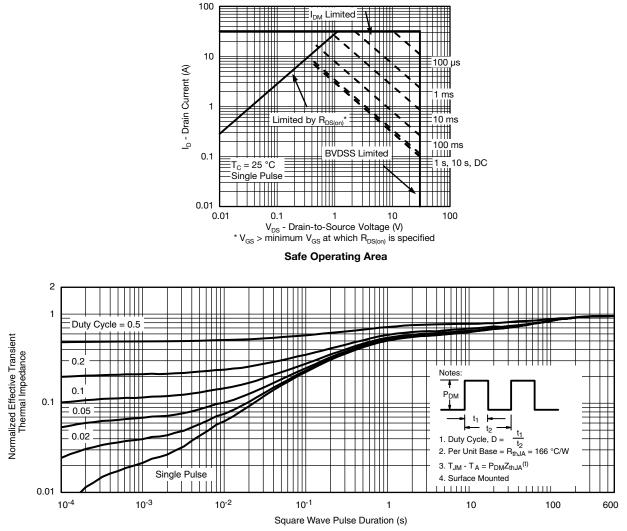
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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

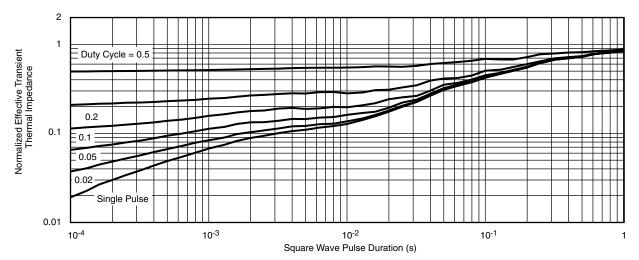


Normalized Thermal Transient Impedance, Junction-to-Ambient



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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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# **SQ2348ES**

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#### **REVISION HISTORY**<sup>a</sup>

REVISION	DATE	DESCRIPTION OF CHANGE		
В	15-May-15	Corrected part marking		

Note

a. As of April 2014



# Package Information

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## SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES			
Dim	Min	Max	Min	Мах		
Α	0.89	1.12	0.035	0.044		
A <sub>1</sub>	0.01	0.10	0.0004	0.004		
A <sub>2</sub>	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E <sub>1</sub>	1.20	1.40	0.047	0.055		
е	0.95	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024		
L <sub>1</sub>	0.64 Ref		0.025 Ref			
S	0.50 Ref		0.020 Ref			
q	3°	8°	3°	8°		



# Application Note 826

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### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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